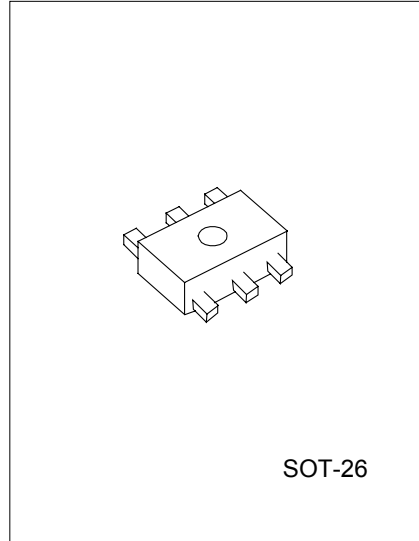
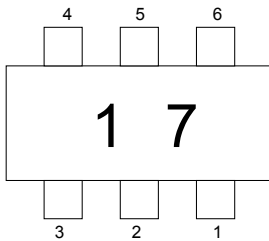


GENERAL PURPOSE DUAL TRANSISTOR

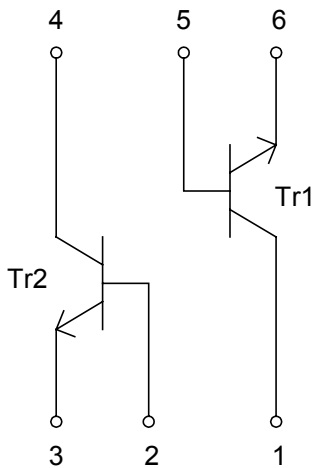
FEATURES

- *Two 2SD1484K chips in an SMT package.
- *Mounting possible with SMT3 automatic mounting machine.
- *Transistor elements are independent, eliminating interference.
- *High collector current. Ic=500mA
- *Mounting cost an area can be cut in half.

MARKING



- | | |
|-----------------------|----------------------|
| PIN 1 : Collector (1) | PIN 4: Collector (2) |
| PIN 2: Base (2) | PIN 5: Base (1) |
| PIN 3: Emitter (2) | PIN 6: Emitter (1) |



The following characteristics apply to both Tr1 and Tr2.

ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified.)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	60	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _c	500	mA
Collector dissipation	P _d	300 (TOTAL)	mW (note)
Junction Temperature	T _j	150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

Note: 200mW per element must not be exceeded.

ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	BV _{CBO}	I _c =100μA	60			V
Collector-emitter breakdown voltage	BV _{CEO}	I _c =1mA	50			V
Emitter-base breakdown voltage	BV _{EBO}	I _E =100μA	5			V
Collector cutoff current	I _{CBO}	V _{CB} =30V			0.1	μA
Emitter cutoff current	I _{EBO}	V _{EB} =4V			0.1	μA
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =500mA, I _B =50mA			0.6	V
DC current gain	h _{FE}	V _{CE} =3V, I _c =100mA (note)	120		390	
Transition frequency	f _T	V _{CE} =5V, I _E =-20mA, f=100MHz		250		MHz
Output capacitance	C _{ob}	V _{CE} =10V, I _E =0A, f=1MHz		7		pF

Note: Measured using pulse current.

CLASSIFICATION OF h_{FE}

RANK	A	B
RANGE	120-240	240-390

ELECTRICAL CHARACTERISTIC CURVES

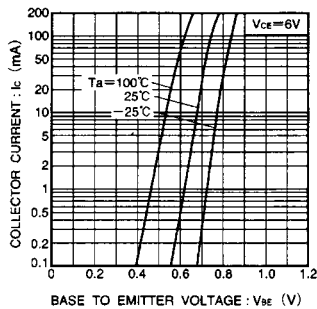


Fig.1 Grounded emitter propagation characteristics

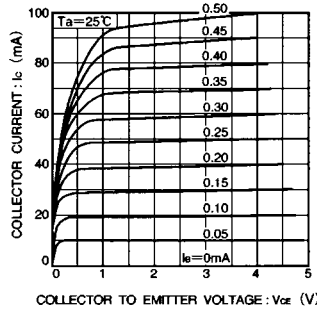


Fig.2 Grounded emitter output characteristics

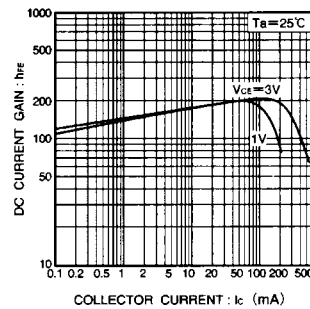


Fig.3 DC current gain vs. collector current (I)

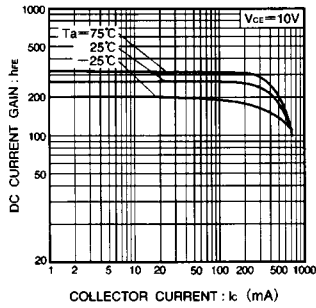


Fig.4 DC current gain vs. collector current (I)

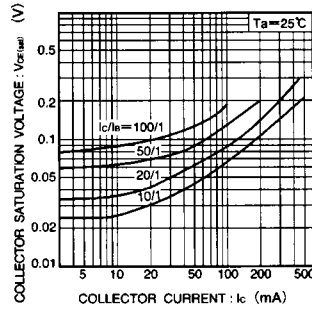


Fig.5 Collector-emitter saturation voltage vs. collector current

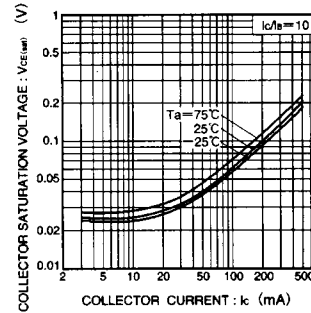


Fig.6 Collector-emitter saturation voltage vs. collector current

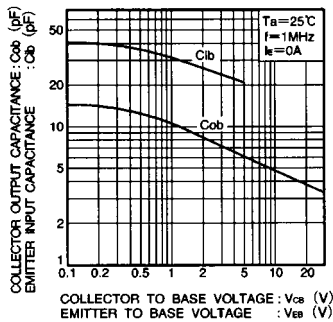


Fig.7 Input/output capacitance vs. voltage

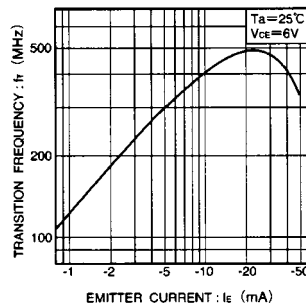


Fig.8 Gain bandwidth product vs. emitter current

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